TA7129AP

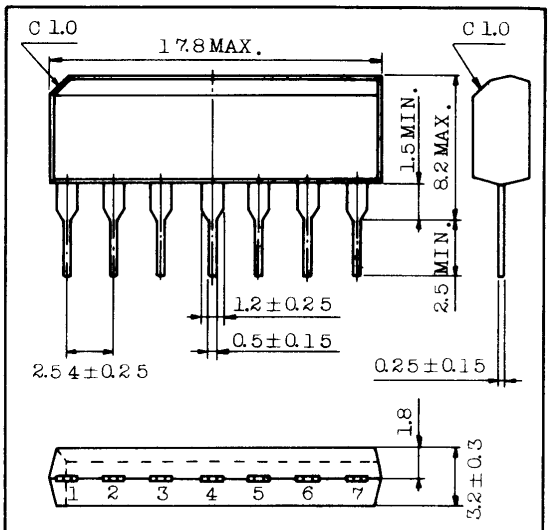
TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT
SILICON MONOLITHIC

VARIOUS HIGH QUALITY PRI-AMPLIFIER.

VOLTAGE AMPLIFIER.

- Low Noise : V_{NI}=0.8μV_{rms}(Typ.)
- High Open Loop Voltage Gain : G_{VO}=92dB(Typ.)
- Low Distortion : THD=0.1%(Max.)
  at V_{OUT}=7V_{rms}, G_V=40dB, f=1kHz.
- The Outer Emitter Resistance of Top Stage Makes, it Possible to get less deviation, better Temperature Characteristic, because the Closed Loop Voltage Gain is decided by the Outer circuit only.

Unit in mm



Lead pitch is 2.54 and tolerance is ±0.25 against theoretical center of each lead that is obtained on the basis of No.1 lead.

JEDEC	—
TOSHIBA	5-18A

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	42	V
Power Dissipation (Note)	P_D	400	mW
Operating Temperature	T_{opr}	-30 ~ 75	°C
Storage Temperature	T_{stg}	-55 ~ 125	°C

(Note) Derated above Ta=25°C in the proportion of 4mW/°C.

ELECTRICAL CHARACTERISTICS (V_{CC}=35V, Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Current	I_{CC}	1	V_{IN}=0	-	3.5	4.7	mA
Voltage Gain (Open Loop)	G_{VO}	1	V_{IN}=-85dBm, f=1kHz	87	92	-	dB
Maximum Output Voltage	V_{OM}	2	f=1kHz, THD=0.1%	7.0	9.0	-	V_{rms}
Equivalent Input Noise Voltage	V_{NI}	3	RIAA equalizer R_g=2.2kΩ, f=1kHz	-	0.8	1.5	μV_{rms}

EQUIVALENT CIRCUIT